Article 19 claim Amendment

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Amendment of the claims under Article 19 (1) (Rule 46)

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Dear sir,

The Applicant, who received the International Search Report relating to the above identified International Application transmitted on 16 August 2005, hereby files amendment under Article 19 (1) as in the attached sheets.

We hereby would like to add the claim 8.
The claims 1, 2, 3, 4, 5, 6, 7 are retained unchanged.

The Applicant also files as attached herewith a brief statement explaining the amendment and indicating any impact that amendment therein might have on the description.

Very truly yours,

Hiroyuki Kurihara

Attachment:
(1) Amendment under Article 19 (1) 1 sheet
(2) Brief Statement 1 sheet

AMENDED CLAIMS

1. A composite for forming a ferroelectric thin film made of a colloidal solution applicable to the metal organic deposition method containing an organometallic compound including metal constituting a ferroelectric thin film, comprising:

at least water other than water of crystallization in the organometallic compound.

2. The composite for forming a ferroelectric thin film according to claim 1,

wherein molar quantity of the water other than the water of crystallization in the organometallic compound is 1 to 10 times as much as total molar quantity of the metal contained in the colloidal solution.

3. The composite for forming a ferroelectric thin film according to claim 2,

wherein the molar quantity of the water other than the water of crystallization in the organometallic compound is 5 to 7 times as much as the total molar quantity of the metal contained in the colloidal solution.

4. A ferroelectric thin film made of the composite for forming a ferroelectric thin film according to any one of claims 1 to 3.

5. A liquid-jet head comprising:

a piezoelectric element including the ferroelectric thin film according to claim 4 as a piezoelectric actuator that ejects a liquid.

6. A method of manufacturing a ferroelectric thin film comprising:

adding water other than water of crystallization in an organometallic compound to a colloidal solution applicable to the metal organic deposition method containing the organometallic compound including metal constituting a ferroelectric thin film;

coating the obtained composite for forming a ferroelectric thin film on a target object; and

forming the ferroelectric thin film by drying and sintering the composite for forming a ferroelectic thin film on the target object.

7. The method of manufacturing a ferroelectric thin film according to claim 6,

wherein the composite for forming a ferroelectric thin film is conveyed to a nozzle connected to a tank pooling the composite for forming a ferroelectric thin film by introducing dry inert gas into the tank, and the composite for forming a ferroelectric thin film is dropped onto the rotating target object from the nozzle when coating the composite for forming a ferroelectric thin film on the target object.

8. (Additional) The method of manufacturing a ferroelectric thin film according to claim 6,

wherein the water other than the water of crystallization is added after addition of a hydrolysis inhibitor to the colloidal

solution.

STATEMENT PURSUANT TO ARTICLE 19(1)

Claim 8 defining addition of the water other than the water of crystallization after addition of a hydrolysis inhibitor to the colloidal solution is added as a dependent claim on claim 6. The amendment of addition of claim 8 is based on the description in the paragraph [0038] of this specification.